19 May (sun)
Registration 12:30-18:00
Special Lecture I 15:00-16:00
Coffee Break 16:00-16:30
Special Lecture II 16:30-17:30
Reception 18:00-20:00

20 May (Mon)				
Room A				
CSW 2019 Opening 8:30-8:40				
CSW 2019 Plenary MoPLN1-1 8:40-9:20				
CSW 2019 Plenary MoPLN1-2 9:20-10:00				
Coffee Break 10:00-10:30				
CSW 2019 Plenary MoPLN2-1 10:30-11:10				
CSW 2019 Plenary MoPLN2-2 11:10-11:50				
IPRM/ISCS Award Ceremony & Photo 11:50-12:30				
Lunch Time 12:30-14:00				
Room A	Room B	Room C	Room D	Room E
MoA3 14:00-16:00 Advanced Lasers	MoB3 14:00-16:00 Growth of Nitrides	MoC3 14:00-16:00 Electrical and Optical Devices of 2D Materials	MoD3 14:00-16:00 GaN and Related Technologies I	MoE3 14:00-16:00 Oxides: Structures and Properties
Poster Session I 16:00-18:00				
Social Program I 18:00-19:00				

21 May (Tue)				
Room A	Room B	Room C	Room D	Room E
TuA1 8:30-10:30 Nanomechanics, Thermal and phonon transport	TuB1 8:30-10:30 GaN MOS Power FETs	TuC1 8:30-10:30 Growth and Sensor of 2D Materials	TuD1 8:30-10:30 Ga2O3 Bulk and Epitaxial Growth	TuE1 8:30-10:30 hBN : Growth I
Coffee Break 10:30-11:00				
TuA2 11:00-12:30 Superconductor-Semiconductor Hybrid Structures	TuB2 11:00-12:30 Quantum Dot Lasers	TuC2 11:00-12:30 RF and on-Si Technology	TuD2 11:00-12:30 Ga2O3 Process and Characterization	TuE2 11:00-12:30 hBN : Point Defects
Lunch Time 12:30-14:00				
Room A	Room B	Room C	Room D	Room E
TuA3 14:00-16:15 Advanced Photonic Integration	TuB3 14:00-16:00 Epitaxial Growth on Group IV Substrates	TuC3 14:00-16:00 Characterization of Nanostructures	TuD3 14:00-16:00 Ga2O3 Electrical Devices	TuE3 14:00-16:00 hBN : Spectroscopy and Growth II
Poster Session II 16:00-18:00				
Social Program II 18:00-19:00				

22 May (Wed)				
Room A	Room B	Room C	Room D	Room E
WeA1 8:30-10:00 GaN and Related Technologies II	WeB1 8:30-10:00 Photovoltaic and LED	WeC1 8:30-10:00 Nanowire Devices	WeD1 8:30-10:00 Quantum Dots and Coherent dynamics	WeE1 8:30-10:00 Organic Devices
Coffee Break 10:00-10:30				
WeA2 10:30-12:00 GaN and Related Technologies III	WeB2 10:30-11:45 Mid Infrared Photonics	WeC2 10:30-12:00 Fabrication of Nanostructures	WeD2 10:30-12:00 Spin Transport and Dynamics	WeE2 10:30-12:00 THz Devices
Excursion 12:30-18:00				
Banquet 18:30-21:00				

23 May (Thu)				
Room A	Room B	Room C	Room D	Room E
ThA1 8:30-10:30 Growth of Nanostructures and Quantum-Effect Devices	ThB1 8:30-10:30 Novel Photonics	ThC1 8:30-10:30 Oxides: Doping	ThD1 8:30-10:30 GaN and Related Technologies IV	ThE1 9:00-10:30 Organic and Perovskite materials
Coffee Break 10:30-11:00				
ThA2 11:00-12:30 Advanced Epitaxial Growth Techniques of III-V Materials	ThB2 11:00-12:30 Photodetectors	ThC2 11:00-12:30 GaN Power Devices and Characterization		
Closing and Student Award Ceremony 12:45-13:30				

A: Epitaxy, fabrication, and related technologies
B: RF electron devices
C: High power electron devices
D: Photonic devices and related technologies
E: Physics, spintronics, and novel device concepts
F: Nanocharacterization and nanostructures
G: GaN and related semiconductors
H: Oxide semiconductors
I: Nanocarbon and novel 2D materials
J: Organic semiconductors and flexible materials
SS1: (Special session) Gallium oxide: materials and devices
SS2: (Special session) Hexagonal boron nitride